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Chapter 1

Introduction

Throughput, scalability, and low latency are the most important features of present and future computer and communication networks. These are achieved by employing point-to-point links and switches (routers), as the building blocks of the networks. A switch is a device connected to a number of incoming and outgoing links whose function is to route incoming packets to the appropriate outgoing link(s).

Frequently, two or more incoming packets that arrive simultaneously need to be routed to the same outgoing link. In such occasions, one of the packets is forwarded to the outgoing link, while the others are *buffered* inside the switch and transmitted at a later time.

Many architectural alternatives for organizing these buffers exist, of which the most important are input queueing, output queueing, crosspoint queueing and shared buffering. Shared buffering performs best among the alternatives, but it needs to use high throughput buffers. Such buffers are usually implemented as multiple interleaved banks of memory or as a single memory with a large word size (wide memory). A new, better method for building high throughput memories, called pipelined memory, was recently introduced by Katevenis (see [KaVE95]). This thesis describes the full-custom CMOS implementation of a pipelined memory for an 8×8 switch and its post-fabrication testing. Earlier, two other implementations of the pipelined memory were realized using discrete components and standard cells as the buffer memory of the Telegraphos [Kate94] I and II switches.

1.1 Switch Queueing Architectures

Instead of buffering, some switches use *deflection routing*. That is, the packets that can not be forwarded to the required outgoing link are transmitted through other links that are idle at the time. Depending on the network topology and on the routing algorithm, the deflected packets either use another path to reach their destination, or they return back to the switch that "deflected" them, hoping that they will succeed to pass through this time.

In effect, deflection routing uses the links to delay the packets until the requested port

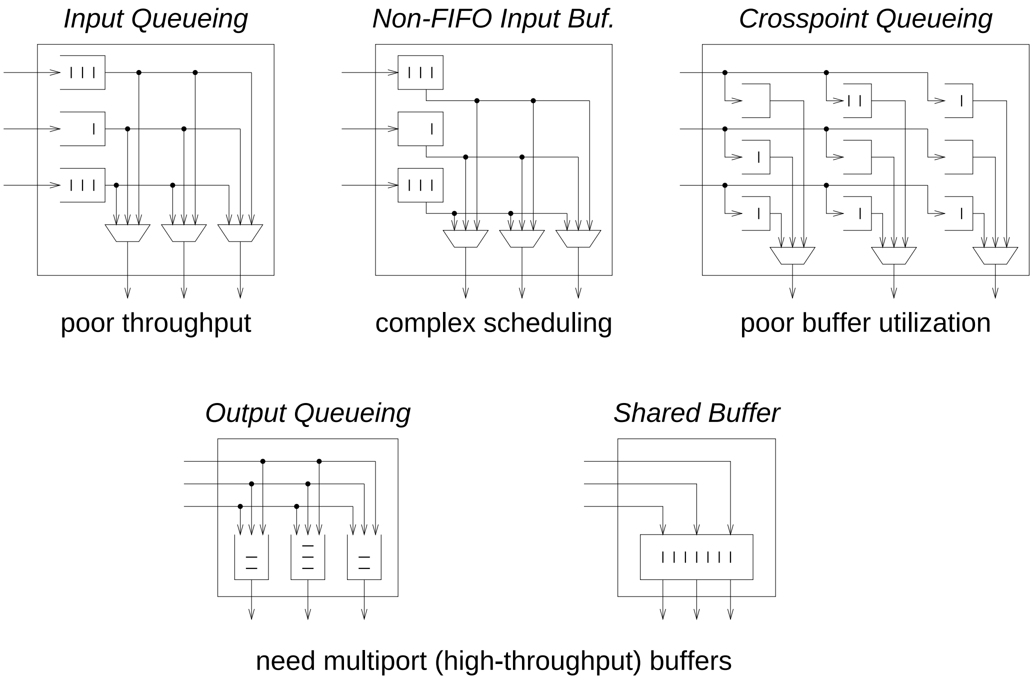


Figure 1.1: Switch queueing architectures.

is free, whereas buffering uses on chip memory for the same purpose. In VLSI technology, inter-chip communication is more expensive than on-chip memory, as it is well known that adding more pins to a chip is costlier than placing more memory in it. In addition, the minimum delay for transmitting and then receiving back a deflected packet is probably longer, and the operation more complicated, than an on-chip memory write and read. For these reasons, this work considers only switches that use buffering.

With regard to buffering, four basic alternatives are available to switch architects: input, output, cross-point, and shared buffering, with FIFO or non-FIFO management (see figure 1.1).

Input FIFO buffering, referred to as *input queueing*, is the simplest architecture; each incoming link feeds one queue dedicated to it. Unfortunately, it is also the worst performing one, due to *head-of-line blocking*: if the first packet in the queue is blocked as a result of an output conflict, the packets behind it are also blocked, even if the outgoing links they are destined to are currently idle. Input buffering without FIFO management yields better performance than input queueing [AOST93] [TaCh93] [LaSe94], but even then output throughput is usually less than optimal. In addition, these non-FIFO input buffers and their scheduling are more complicated than those of input queueing [AOST93] [TaCh93] [LaSe94] [TaFr88].

In *cross-point queueing* there is one FIFO buffer for each pair of input and output ports. In this scheme, each output can select a packet for transmission, among the queues that correspond to it, independent of the other outputs. Thus, the utilization of output throughput is optimal in this architecture. The problem with cross-point queueing is that many buffer memories are needed, yielding more circuit overhead and a larger total memory capacity than that required by other, similar-performing architectures.

The buffer organization where every output port is associated with only one queue is called *output queueing*. In this architecture, each output buffer must have enough throughput to be able to receive packets from all inputs simultaneously, in the worst case. This organization achieves optimal output throughput and better memory utilization than cross-point queueing, but the required buffer throughput is much higher than that of the aforementioned architectures.

Finally, *shared buffering* uses one central buffer for all of the input and output ports. This buffer must have enough throughput to receive packets from all inputs and to provide packets to all outputs, simultaneously. Shared buffering not only achieves optimal output throughput, like cross-point and output queueing, but it also achieves the best memory utilization [HlKa88]. Thus, shared buffering is the best switch buffer architecture for high performance switches. The cost of implementing this buffer organization is not too high, as the existing techniques and the recent pipelined memory architecture are not more expensive to build than the implementations of the other organizations (see [KaVE95], section 5.1).

1.2 This Thesis

In this work we present the design of a pipelined memory for an 8×8 switch, with a packet size of 256 bits, and a total storage of 256 packets. It is designed using full-custom VLSI techniques and a digital CMOS $1 \mu m$ technology. Our implementation is simulated to work at 100MHz in the typical conditions, yielding a total buffer throughput of 25Gbits/sec. Four basic alternative organizations were considered for the floorplan of this pipelined memory, and although only one of them is implemented, the others may be preferable for different buffer specifications. The implemented pipelined memory was included in a test chip which also contains interface and control circuits that were designed with standard cells. This chip tests all the operations of the pipelined memory at full speed, without requiring expensive external circuitry.

In chapter 2 we summarize the existing techniques for implementing high throughput memories and describe the new pipelined memory organization. Chapter 3 covers the design, floorplan organization, and other implementation issues of a pipelined memory for an 8×8 switch, and chapter 4 describes the test chip, where this pipelined memory is included. In chapter 5 we present the results of post-fabrication testing, and we conclude in chapter 6, where we also give ideas for extending this work.

Chapter 2

High Throughput (Multiport) Memories

True multiport memory is overly expensive in silicon area, because of the extra memory cell transistors, bit-lines and word-lines that have to be added. Thus, true multiport memories are only used for building small memory blocks like processor register files, which is not the case for switch buffers. Therefore, switch architects use pseudo-multiport memories: interleaved memory and wide memory.

This chapter describes the existing multiport memory organizations and the pipelined memory organization proposed in [KaVE95].

2.1 Pseudo-Multiport Memories

We call *interleaved memory* the organization of a memory into multiple interleaved single ported banks. Interleaved means that the address space is dispersed among the banks, with the most usual case being that consecutive addresses correspond to different memory banks. In this way, the number of simultaneous memory accesses is equal to the number of the banks, if these memory accesses request data residing in different banks. Many switches use interleaved memory, either as a shared buffer, or for building high throughput output queues: "Knockout" [YeHa87], "Prelude" [DeCS88] (for reads only), [Turn93], [Mirf95], and "PRIZMA" [DeEI95].

Instead of achieving high-throughput using multiport memory built from several single-ported memories, a single memory with a large word size can be used (*wide memory*). One can view this as an interleaved memory in which the same address register is used for all of the banks. This works best when the size of the packet is a multiple of the wide memory word size, so that all accesses are aligned on wide-word boundaries. Wide memory is very attractive for single chip switches, because, in VLSI technology, memories are naturally built wide. The wide memory organization is quite popular: the IBM "Vulcan" [Stun94], the "Prelude" [DeCS88] (when storing packets), and the VLSI ATM switches [Koza91] and [Shob91], all use this organization.

A shared buffer ATM switch employing wide memory [KaSC91], was designed by our

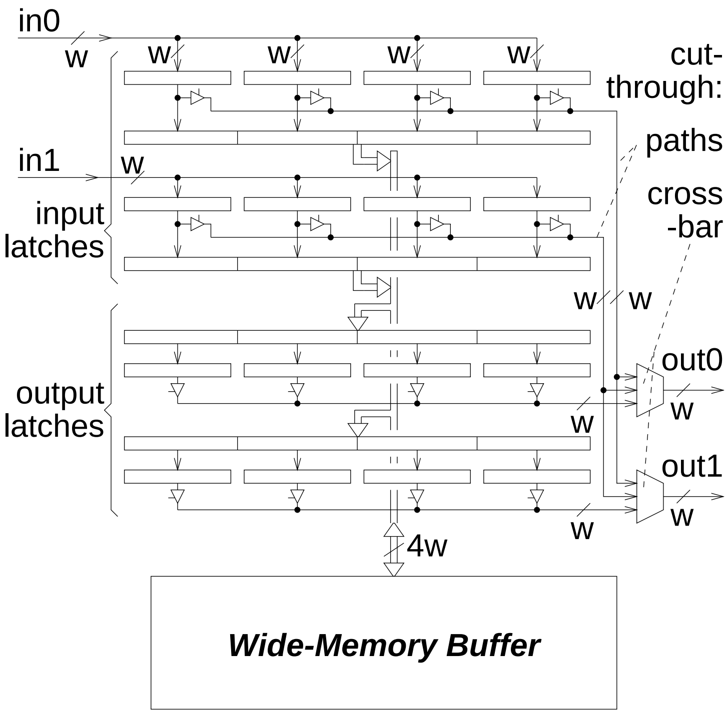


Figure 2.1: The wide memory buffer of [KaSC91].

research group. Figure 2.1 shows its buffer, the incoming and outgoing links, and their associated circuits, shortened to a 2×2 switch for simplicity; [KaSC91] is a 4×4 switch. We assume that packets are transferred on the links in the form of multiple words of w bits each, one word per cycle time, and that the link cycle time is equal to the memory cycle time. In the simple example of figure 2.1, the link throughput is 1 word/cycle, the packet size is 4 words (or a multiple thereof), and the width of the buffer memory is 4 words. Hence, the memory throughput is 4 words/cycle, which is equal to the aggregate incoming and outgoing link throughput. Since in the wide memory organization a packet can be stored or retrieved as a whole, it must first be fully assembled and then stored in memory or, for transmission, it must first be read into a latch and then transmitted, one word at a time. This assembly and disassembly is performed in the input and output latches. Double buffering is essential for the incoming packets, because at the time the last word of a packet has been received, it is not guaranteed that the wide memory will be available for storing the packet, while a new packet may arrive from the same link, overwriting the previous one. This is possible, since we assume that packet arrivals are not synchronized. As can be seen in figure 2.1, double buffering is also used in [KaSC91] for the outgoing link circuits in order to allow transmissions of packets on the different links to start in the same cycle, if desired; however this is a feature of the switch, not a requirement.

Care was taken to include *cut-through* in [KaSC91]. Cut-through is the capability of a switch to start transmitting a packet just after its header has been received and translated, and before the whole packet has been received. Cut-through is very important for low latency networks, especially those of parallel computers. In order to include cut-through capability to a wide memory shared buffer switch, an incoming packet must be able to be transferred to the appropriate outgoing link from the latches where it is being assembled, through paths other than the wide memory or its data bus. This is because a packet cannot be stored in the buffer before all of it has been received. Thus, tri-state drivers, bus wires and an output crossbar have to be added, as shown in the figure (2.1).

2.2 The Pipelined Memory Organization

The pipelined memory is a simplification of the interleaved memory, resulting when all accesses are sequential. In the pipelined memory, the address used in a bank in the current cycle is the address of the previous bank in the previous cycle. This organization simplifies control compared to interleaved memory and leads to a faster VLSI implementation, with fewer buffer peripheral circuits than wide memory, as will become apparent below.

Figure 2.2 is the pipelined memory equivalent of the wide memory shared buffer of figure 2.1. The pipelined memory version does not have double latches for the incoming links, or any of the outgoing link latches, and, most importantly, it does not need special cut-through circuits. On the other hand, an address register and a memory address decoder are added to each pipeline stage of the new buffer organization.

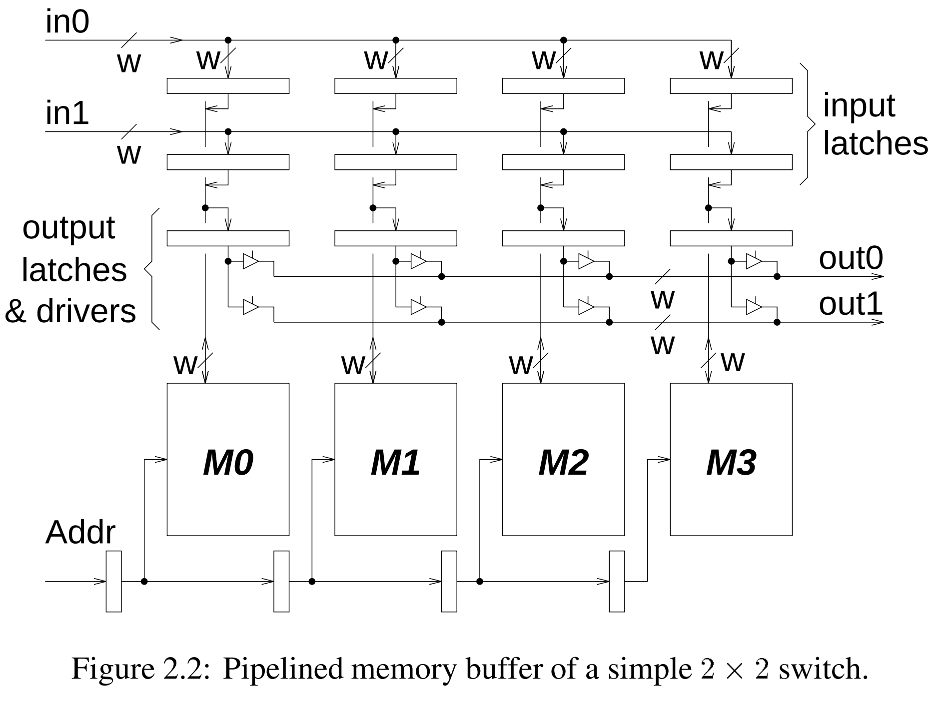


Figure 2.2: Pipelined memory buffer of a simple 2×2 switch.

As we have mentioned already, the shared buffer of a switch must have enough throughput for reading and writing as many packets as the total number of its ports (input and output), during a packet time. Thus, assuming a switch with N incoming and N outgoing links, and a link cycle time equal to the memory bank cycle time, a pipelined memory implementing the switch's shared buffer must have at least $2N$ pipeline stages, and the packet size is equal to $2N$ times the number of parallel data bits transferred by a link, or a multiple of this size.

As a packet arrives at a switch from an incoming link, at the rate of one word per cycle, it is stored in the latches below the link, with the first packet word occupying the leftmost latch and the following words occupying the rest of them from left to right, like a wave. At some cycle after the first word of the packet has been stored in the leftmost latch, and before the arrival of a new packet[1] from the same link, the first packet word will be copied from its latch into the first memory bank M0. In the subsequent cycles, the other words will be written into banks M1, M2, etc., again at the rate of one word per cycle. The words of the same packet are stored at the same address in all the memory banks. Note that a new packet from the same link can start being stored in the link latches or even in the buffer, before the tail of the previous packet has been stored in the buffer. This is perfectly legal and will occur almost invariably if the links are highly utilized. This will not result in any loss of data, because the write of the first packet is initiated before that of the second, and the two "waves" of writes proceed rightward at the same rate. Thus, unlike the wide memory scheme, pipelined memory does not need double buffering. In the same manner as with writes, when a packet is to be transmitted, a read "wave" is initiated at the first memory bank and as soon as the data are read out, they are fed to the bus wires of the selected outgoing link.

The exact cycle when a packet write or read is initiated depends on the outcome of the resolution of contention between the incoming and outgoing links. Normally, the outgoing links are serviced first, so as to maximize link utilization.

In the pipelined memory organization only one latch (with one word per stage) is used for the outgoing links, compared to the one latch per link of wide memory organization. This imposes the restriction that only one packet transmission can be initiated during any cycle; however, the additional packet latency caused by this restriction is negligible as explained in [KaVE95], section 3.4.

Cut-through is automatic in the pipelined memory architecture; if a read happens to be initiated before the packet write wave has reached the last stage, it constitutes cut-through. In the implementation described in chapter 3, the two waves of write and read can even occur simultaneously and as each memory stage is being written to, the new data are also made available at the memory output[2]. Therefore, cut-through is performed through the pipelined memory, saving the considerable silicon area of tri-state drivers, wires and crossbar needed by the wide memory organization.

[1] Assuming a packet size equal to the total word-width of the pipelined memory, not a multiple.

[2] In our implementations the memory banks have two separate unidirectional memory data buses.

2.2.1 Control of the Pipelined Memory

As we have mentioned, the control of the pipelined memory is simpler than that of the other shared buffer organizations. At every cycle, a new operation can start in the first stage M0 of the pipelined memory; we can start reading a new packet for transmission, or we can start writing a packet from the incoming link latches. Loading a new packet into the incoming link's latches is independent from the rest of the pipelined memory operations; many incoming link latches of the same stage can be loaded simultaneously.

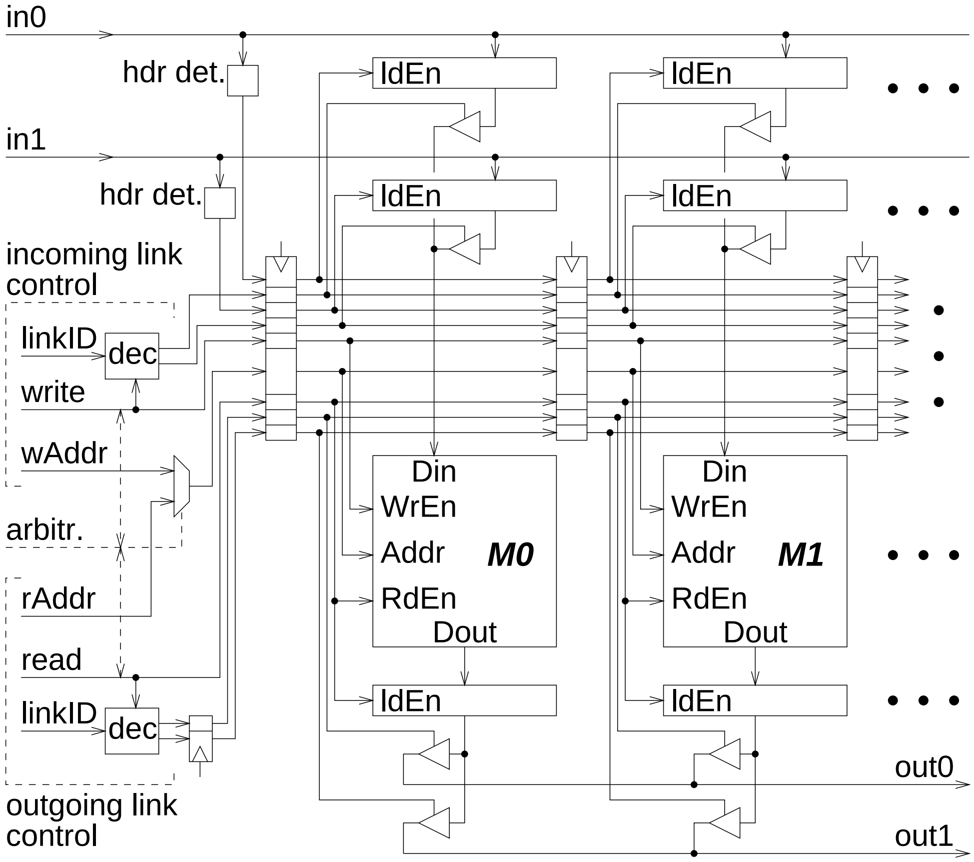
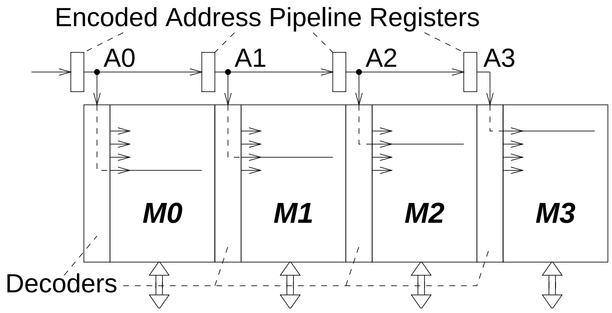


Figure 2.3: Control circuits of the pipelined memory buffer.

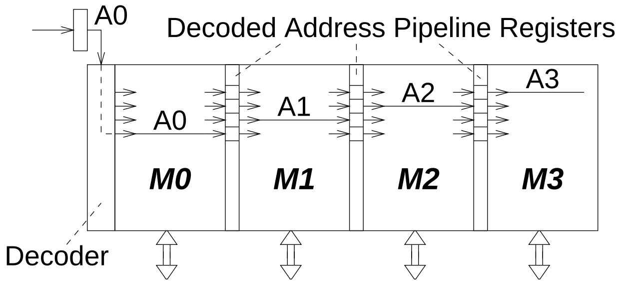
The control signals for the pipelined memory, including the incoming link latches' load enables, are generated for the first stage only. The control signals of the subsequent stages are delayed versions of those of the first stage. Figure 2.3 shows the control signals for the pipelined memory of figure 2.2. Whenever a new packet arrives from a link, it is detected by a link header detector (hdr det.) and the detector's output is used as the load enable signal for the link's latches of the first stage. This signal is then used as the load enable signal for the latches of the subsequent stages, delayed by the appropriate number of cycles. For each read or write initiation, an outgoing or incoming link (linkID) is specified respectively, besides the memory address.

The circuits that provide these signals are independent of the pipelined memory and their choice is orthogonal to this shared buffer organization.

2.2.2 Pipelined Memory Optimizations in VLSI



(a) Traditional



(b) Novel organization and floorplan

Figure 2.4: Pipelined memory in VLSI.

A pipelined memory consisting of traditional RAMs can be arranged as in figure 2.4a. This arrangement has more address decoders than wide memory approach, but it has shorter, and thus faster, wordlines. Actually, the RC delay of the very long wordlines of wide memories makes the memory access cycle long, and so most wide memories are split into many narrower ones, in order to achieve a short memory access time. Thus, for comparable memory access cycles, the area overhead of the additional decoders of the pipelined memory is not very large.

In fact, the extra pipelined memory decoders can be removed if we make the following observation: since the memory stages are placed next to each other, we can transfer the decoded address (the wordlines actually) directly from one stage to the next without redecoding the address at every stage. This is shown in figure 2.4b. With this optimization, each decoder is replaced by a column of wordline pipeline flip/flops, which is often smaller, faster, and may also be less power-consuming, than the decoder.

Figure 2.5 shows a variation of the VLSI pipelined memory that will be appropriate in future very-high-speed IC technologies, when on-chip clock skew will be considerable relative to clock period, and when the buses around the shared buffer and the bit-lines will have high RC delays. Even though these incoming and outgoing link buses have a limited capacitive

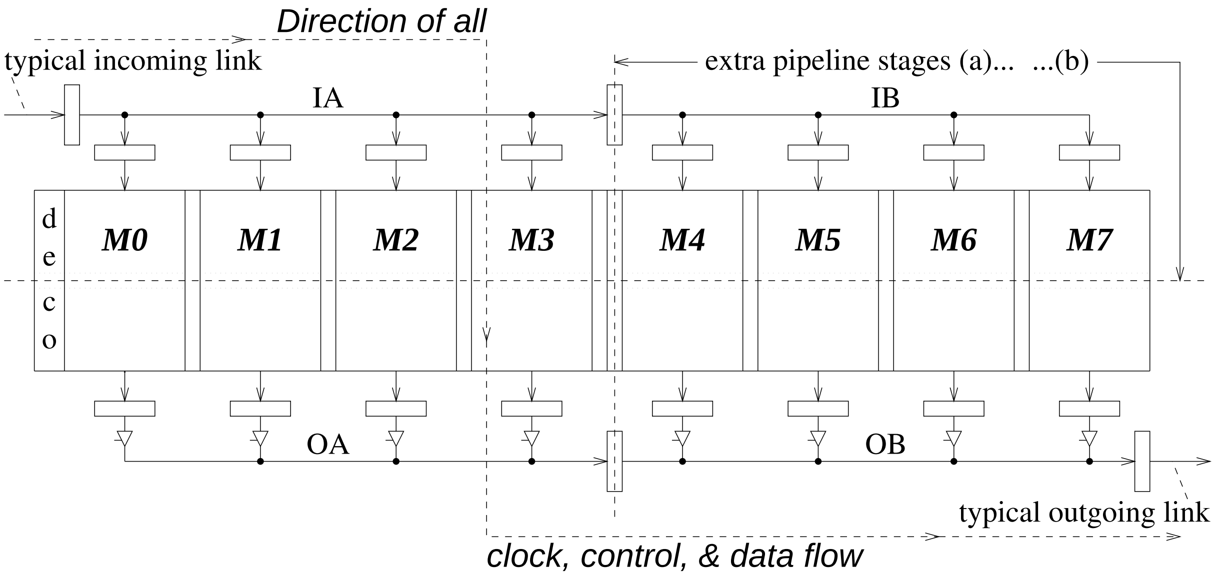


Figure 2.5: Pipelining the input and output buses and the bit-lines of pipelined memory.

load (compared e.g. to RAM word-lines), they will also suffer from RC delays in future high-speed technologies, because of the continued technology trend for shrinking geometries and increasing clock frequencies. At that point, the solution will be to pipeline these buses, as shown in figure 2.5, "extra pipeline stage (a)". In this figure, only one of the input and one of the output buses that will be present in a shared buffer are shown. Each of these buses is divided into two pipeline stages in figure 2.5; more stages are also possible. The number of stages in all input buses must be the same, and it must also equal the number of stages in all output buses. At the point where each I/O bus is split by a pipeline register, one extra decoded-address pipeline register must be inserted into the pipelined RAM. Any word of a packet that is stored in memory stages M0 through M3, in figure 2.5, passes through 2 pipeline registers on its way in, and passes through 3 pipeline registers on its way out. On the other hand, words stored in memory stages M4 through M7 pass through 3 stages on their way in, and 2 registers on their way out. Consequently, the total number of clock cycles spent in going through the I/O pipeline is the same (5 cycles) for all words of every packet; this observation is especially useful in understanding the timing of cut-through operation.

Another feature of the VLSI floorplan of figure 2.5 is that data *always flow in a single direction*, and hence control and clock signals can also be made to always flow in the same direction. To achieve this, the outgoing and incoming links are placed on opposite sides of the memory arrays. By making all signals flow in the same direction and along paths of similar length, it is possible to match (to some degree) the RC delays of the wires that carry these signals, so that their *relative skew* is minimized, which will be crucial in the high-speed technologies of the future.

Finally, if the memory arrays have many rows and the bit-line drive time becomes too long, bit-lines can also be split into multiple pipeline stages, as shown in figure 2.5, “extra pipeline stage (b)”, provided that all memory stages as well as the address decoder are also split in the same manner. This arrangement adds extra pipeline registers in the vertical flow; all packet words passing through the switch do so through an equal number of stages, thus preserving their relative timing. During each memory write or read access, only one of the bit-line stages performs the access, while the others merely pass the information from top to bottom.

Chapter 3

VLSI Implementation of a Pipelined Shared Buffer

The pipelined memory organization is used as the shared buffer of the two Telegraphos [Kate94] switches that were designed by our group. The first is a printed circuit board implemented using FPGAs and commercially available chips, and the second is a single chip design using a 0.7 micron, semi-custom VLSI technology. Since pipelined memory is a regular structure, it can benefit greatly by full-custom design and because in neither of the switch designs, could the VLSI optimizations described earlier be applied, we decided to design another version of the pipelined memory using full-custom techniques.

This chapter presents the specifications of the pipelined memory that we implemented, its microarchitecture and circuits, and the most important decisions that we made at various steps of the design.

3.1 Specifications

We chose to design a pipelined memory for an 8×8 switch, with 16 bits per port, 256 packets of storage, and 256 bits per packet. The first candidate for the packet size was the ATM cell size but that would make our implementation too wide for our $1mum$ technology, without folding the pipelined memory. There is no interest in folding for our purposes though, as it is a simple extension of our implementation and our target in this work was the full-custom implementation of an extendable pipelined memory, not the design of a full ATM switch. Thus, we chose a big enough packet size, leading to a pipelined memory area which is realizable with the technology available to us. Folding is one of the floorplan organizations that were investigated and it is presented in section 3.2.

We aimed at a clock frequency of 100MHz, which we achieved for the typical operating conditions; the worst case clock frequency is 62.5MHz. Thus the aggregate throughput of this memory is 25.6 Gbits/sec for the typical case and 16 Gbits/sec for the worst. For an ATM cell size and the same clock frequency, these would be 42 Gbits/sec and 26 Gbits/sec, respectively.

According to the targeted port number and bits per port, the pipelined memory that we implemented has 16 stages with 256×16 bits of memory in each stage and the packet size is 256 bits. Each of the 8 incoming links consists of a bus of 16 bits of data which run above all stages, plus 2 bits of control that are latched and re-generated at every stage. Of these two control bits, one is the load enable of the incoming link latches and the other enables the corresponding link register to drive the memory input bus. The outgoing links need a single bit of control, which is latched and re-generated at every stage, and, when asserted, drives the 16 outgoing link data wires from the memory output of the appropriate stage. Besides the incoming link data wires and the control signals of the first stage, the other inputs of the pipelined memory are an 8 bit address, a memory write signal, and a clock input. There is no read signal because the memory always performs reads, that is, amplifies the voltage difference on the bitlines and drives the memory output bus, even when a write is performed. In that case, the newly written data are read out. The outputs are the 8 outgoing link buses, which are each 16 bits wide.

Static memory is used instead of the more area efficient dynamic memory for simplicity of our design. Pipelined memory can equally well be implemented with dynamic RAM. Its throughput would have to be somewhat increased so that refreshing will not interfere with its normal operation, but this may not be necessary, as the time a packet waits in a switch buffer will normally be less than the charge decay time of dynamic memory cells.

The target technology is the European Silicon Structures (ES2) $1.0\mu m$ CMOS technology with two metal layers and one polysilicon layer, operating at a supply voltage of 5 volts. The SPICE model parameters we had for this technology were old and they had significant differences in some parameters between consecutive versions, which made us suspicious about their accuracy. So we were very conservative designing our circuits, to be assured that they work under all conditions. Ironically, we received a new version of these parameters just as we were submitting the test chip for fabrication. For accuracy we will use the new parameters for the circuit simulations that will be presented, but the reader should keep in mind that all of the circuits were designed and optimized by simulating them with the previous model version.

3.2 Floorplan Organization

We found many ways to physically organize the pipelined memory. The most important of them are described here, using the specifications stated earlier (port number, bits per port, etc.). In these organizations, we assume that the incoming link latches and the memory input drivers are physically placed under the incoming link wires and the same holds for the outgoing link drivers. This assumption is realistic, and it has been easily achieved in our design.

In the following diagrams describing these organizations, the circles are either incoming link latches and memory input drivers, or outgoing link drivers, while the small rectangles are pipeline latches. Moreover, solid lines represent data wires and dashed lines represent control wires.

3.2.1 Alternatives Considered

First Alternative Organization

The first organization is shown in figure 3.1. This is the organization that was finally chosen for implementation. The memory banks are arranged as 256 bits high by 16 bits wide each, and they are placed side by side in a row, with wordline pipeline latches between them. The bitline drivers, the incoming links, and their associated circuits are placed above the memory banks, whereas the sense amplifiers and the outgoing links are placed below the memory banks.

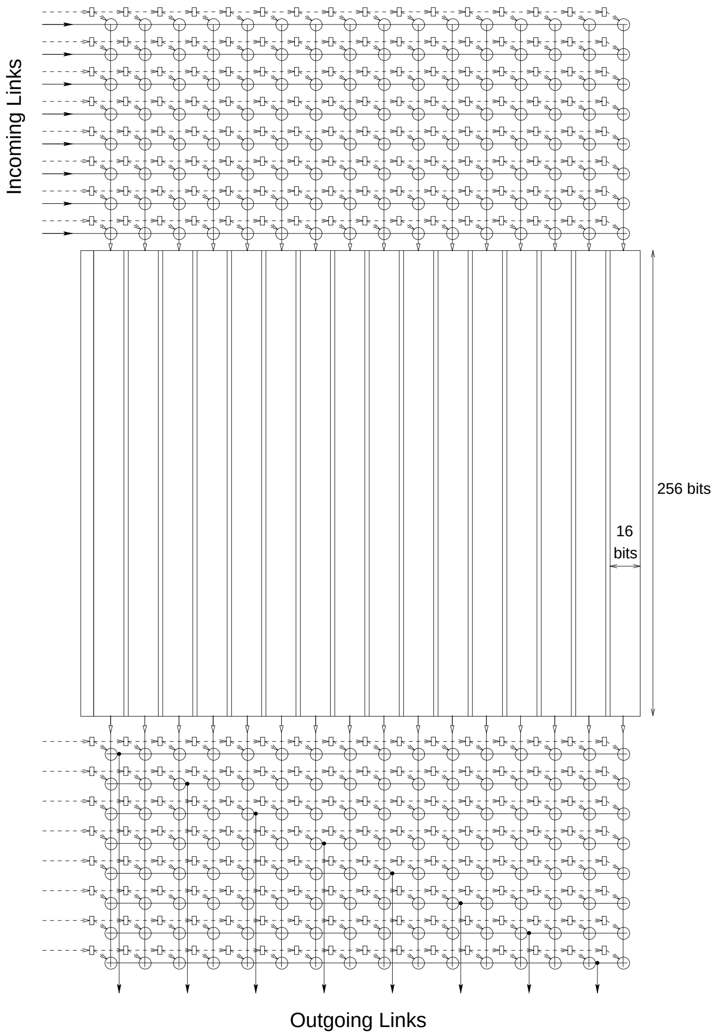


Figure 3.1: First alternative organization of the pipelined memory.

Although it may seem natural for the outgoing links to have their outputs on the right and bottom end of the block, this is not the case in our implementation. These link wires are long and carry large capacitance, so they need buffers (inverters) for amplification and effective driving of the external circuits. These buffers are hard to place horizontally next to the link buses, because the latter have a very small vertical pitch as they are placed with the minimum allowed distance between them. Our solution is to add a vertical wire as an extension to each link wire and route this extension through the outgoing link driver area to the bottom side of the block. In this way, the buffers are placed below the links, making their outputs available for connection at the bottom end of the pipelined memory block. The extra wire added does not increase the outgoing link wire capacitance too much because it is very short compared to the link wire's horizontal length.

Using a square memory cell layout, this microarchitecture leads to an almost square shared buffer block: there are 256 bits of memory in each dimension, and the total width of the 15 wordline pipeline latches plus the decoder is comparable to the total height of the incoming and outgoing link area.

Second Alternative Organization

An alternative way to organize the pipelined memory (see figure 3.2) is to split all of the memory banks in two parts, so that half of the packets are stored in the top row of bank segments and the rest in the bottom row. The links run horizontally between the two memory rows.

This architecture has the advantage of having half-height memory blocks with the bitlines carrying half the capacitance relative to the previous organization, which leads to a faster memory access time. There are some disadvantages though: the incoming and outgoing links are on the same side of the memory banks and consequently both the memory input and output buses cross them, making their cell's layouts wider than those of the first microarchitecture. In addition, the memory inputs and outputs are on the same side, as well, complicating the layout of the bitline drivers and sense amplifiers. The outgoing link buffers must be placed horizontally, as the vertical direction is now blocked by memory. Finally, the bitline drivers and the sense amplifiers are duplicated, since each memory bank is split in two.

Third Alternative Organization

The third organization (figure 3.3) is formed by placing half of the pipeline *stages* in one row and the other half in another, with the incoming and outgoing links placed in between. This *folded* organization is of interest in case where the width of the pipelined memory is much larger than its height. This can happen when the packet is large and/or when there are many pipeline stages.

The layout of this organization would be too tall, if we used a memory cell with an aspect ratio of 1, since there are four times more memory cells in the vertical dimension than in the

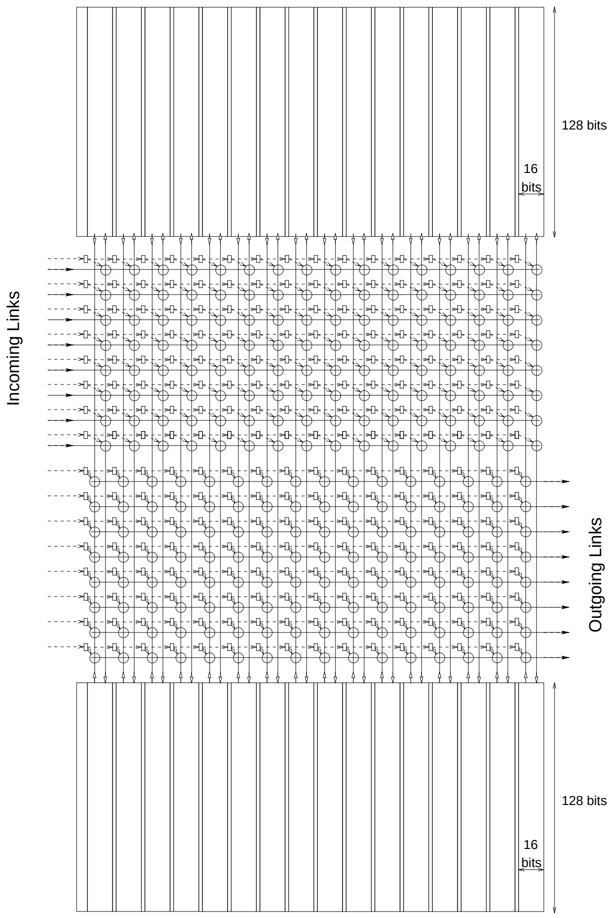


Figure 3.2: Second alternative organization of the pipelined memory.

horizontal, for a total memory size equal to that of the other organizations. Thus, the memory cell layout must be wide and short. Alternatively, column decoding/multiplexing can be used to achieve an aspect ratio close to 1 for the whole pipelined memory block. The disadvantages of the second organization concerning the layout of the peripheral circuits, are also present in this organization, but they are not important any more, as the width of the memory cell, and thus the width of the link associated cells, is inherently large. This organization also needs an extra decoder for the second row of pipeline stages.

Fourth Alternative Organization

Finally, the fourth organization (figure 3.4) is a variation of the first, but the basic idea behind it can be applied to the other microarchitectures as well. This *bit-sliced* organization divides each memory bank *word* and each link data bus in two (or more) parts. In this way, two pipelined memories of the first organization are formed, with half the word size and the link

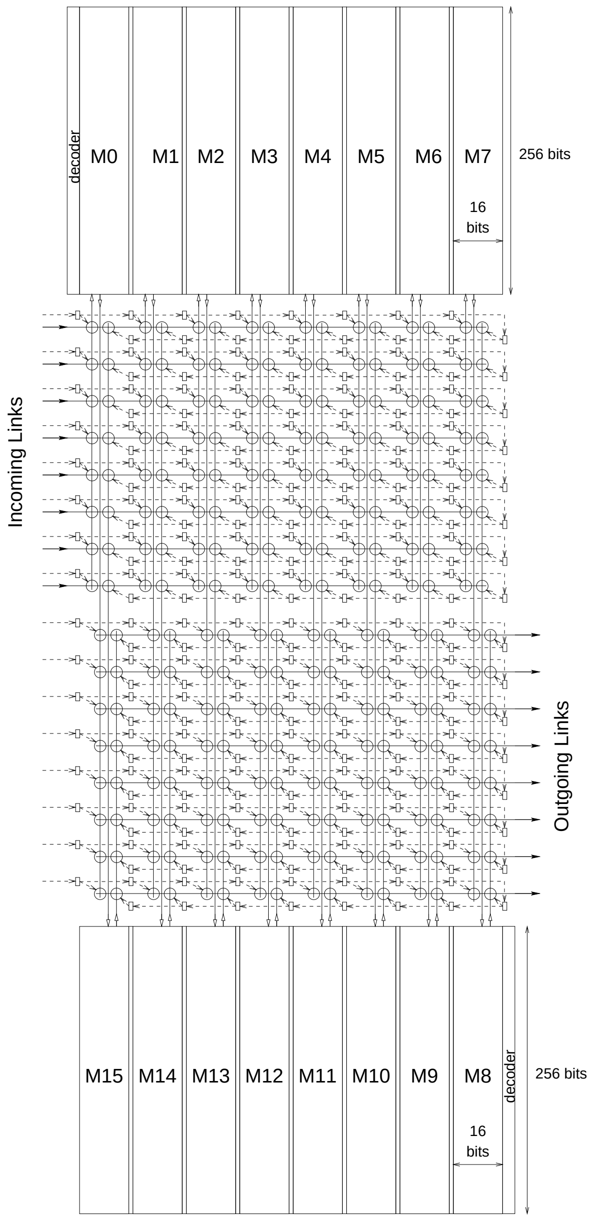


Figure 3.3: Third alternative organization of the pipelined memory.

data-bus width for each. The memory arrays of the two banks can be rearranged to use column decoding/multiplexing in order to keep the aspect ratio of the whole block close to 1.

Bit-slicing the pipelined memory reduces the link area by the factor of slicing. Let N be the number of incoming or outgoing links, w the width of the links' data-bus (and the word size of each memory stage), and $2Nw$ the total width, in bits, of the pipelined memory. Then, for the first organization, the area of the incoming (or the outgoing) links would grossly be Nw

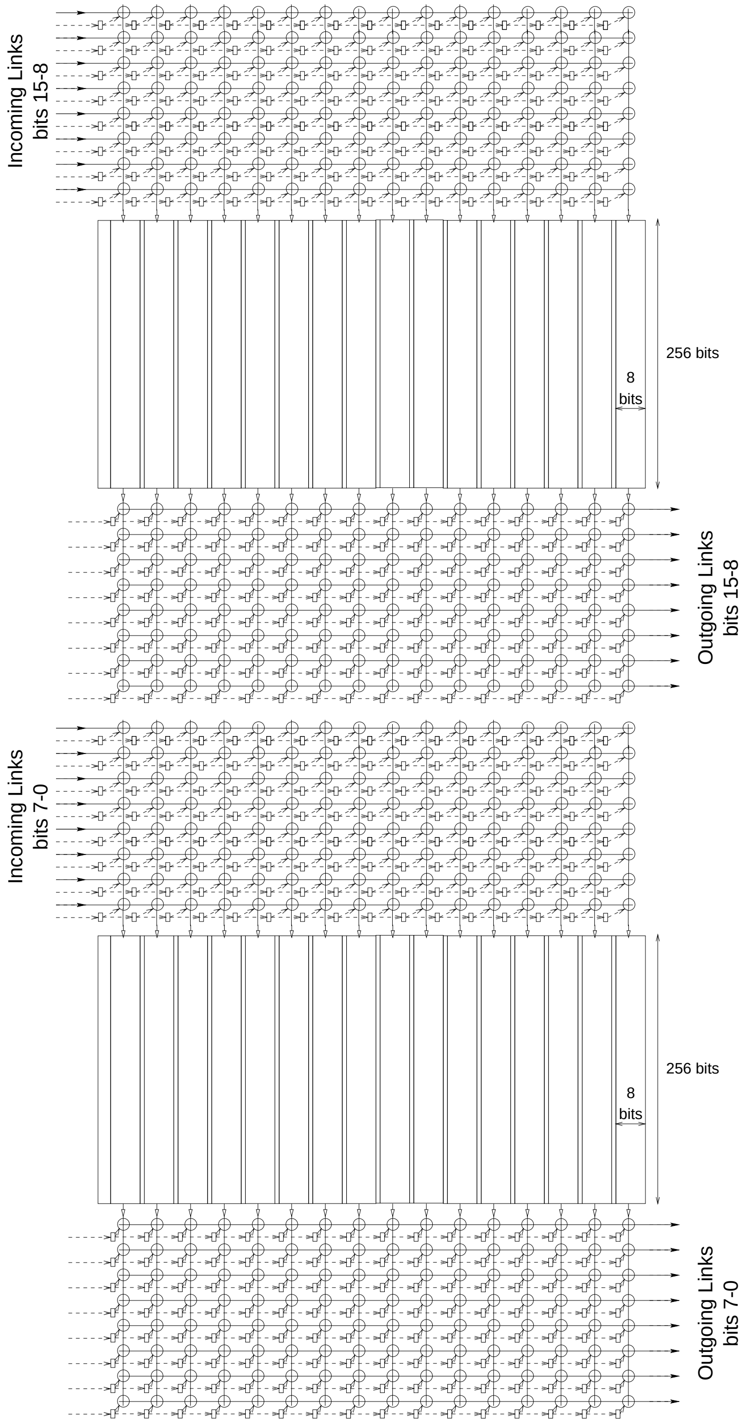


Figure 3.4: Fourth alternative organization of the pipelined memory.

wires vertically times $2Nw$ memory cells horizontally, that is a total of $2N^2w^2$. If this pipelined memory is sliced in s parts ($1 \leq s \leq w$), then each of these slices has an incoming (or outgoing) link area of $N(w/s)$ wires vertically times $2N(w/s)$ memory cells. The total link area for all the slices would be $s \cdot N(w/s) \cdot 2N(w/s) = (2/s)N^2w^2$.

Although the above results show that the link area is minimized when the pipelined memory is split in the maximum number (w) of slices, this is not true, because the above area estimates do not take into account the control wires needed for each link (load enable, memory input bus drive, and outgoing link bus drive) which contribute a factor of N times the horizontal width, and the area of the sense amplifiers and bit-line drivers (a big constant), which must be added to each sliced memory bank. Thus, bit-slicing is an interesting idea when the link data buses and memory bank words are wide, and saves considerable link area in many cases, but it cannot be applied to its extreme. In addition to the area savings, the small memory banks of this organization will have a shorter memory access cycle relative to those of the first.

We chose to implement the first organization, because it is the most straightforward, the easiest to lay out, and the other organizations are simple extensions of it.

3.2.2 Floorplan of the Implemented Memory

The detailed floorplan of the pipelined memory that we implemented is shown in figure 3.5. The width of each decoded address pipeline register is 2.2 times smaller than that of a normal address decoder, justifying the use of the first instead of the latter.

	Semi-custom	Full-custom	times better
Core Area	$47mm^2$	$31mm^2$	1.5
Periph. Ckt Area	$128mm^2$	$12mm^2$	10
Total Area	$175mm^2$	$43mm^2$	4
Cycle Time (worst case)	40ns	14ns	3
Aggregate Throughput	10Gbps	30Gbps	3

Table 3.1: Full-custom versus semi-custom comparison: 256-cell pipelined memory for a 16×16 ATM switch.

Table 3.1 is a comparison of a semi-custom and a full-custom implementation of the pipelined memory for a 16×16 ATM switch, with 256 cells storage, using the ES2 0.7 micron CMOS technology. The areas are calculated by transforming our 0.7 micron semi-custom Telegraphos II switch and this 1 micron full-custom design to the ATM cell size and the 0.7 micron technology. The full-custom implementation would be 3 times faster and 4 times smaller than the semi-custom, while the full-custom peripheral area would be 10 times smaller relative to that of the semi-custom. These area savings relative to the standard-cell version stem from the use of dynamic latches for storing the incoming packets, the use of precharging (actually, domino logic [KrLL82]) for all long wires that have multiple drivers (e.g. outgoing link buses), and the overlap of the peripheral circuitry with the link wire routing.

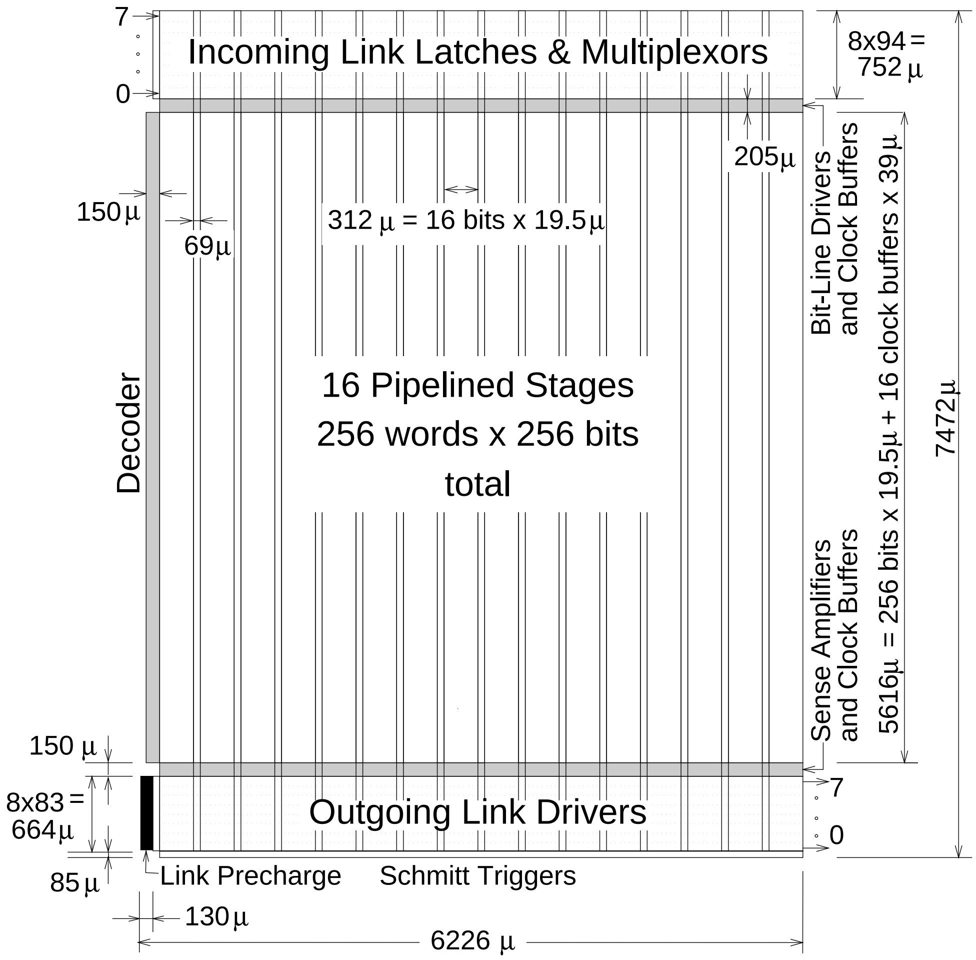


Figure 3.5: Floorplan of the pipelined memory that we implemented.

3.3 Detailed Circuit Description and Simulations

Figure 3.6 shows the circuits for one bit of the pipelined memory, the control signals and the clock phase when they are activated.

The clocking scheme that we use is pseudo-two-phase clocking, where only one phase is distributed in the full-custom block and the other is generated locally, wherever it is needed. Pseudo-two-phase is the simplest way to implement a two-phase clock, while the tri-state dynamic latches and the edge triggered latches that we use are both insensitive to the short overlap of the two phases.

Tables 3.2 and 3.3 summarize the clock phase when the basic operations are performed, and the polarity of the control signals and the clock phase when they are asserted respectively,

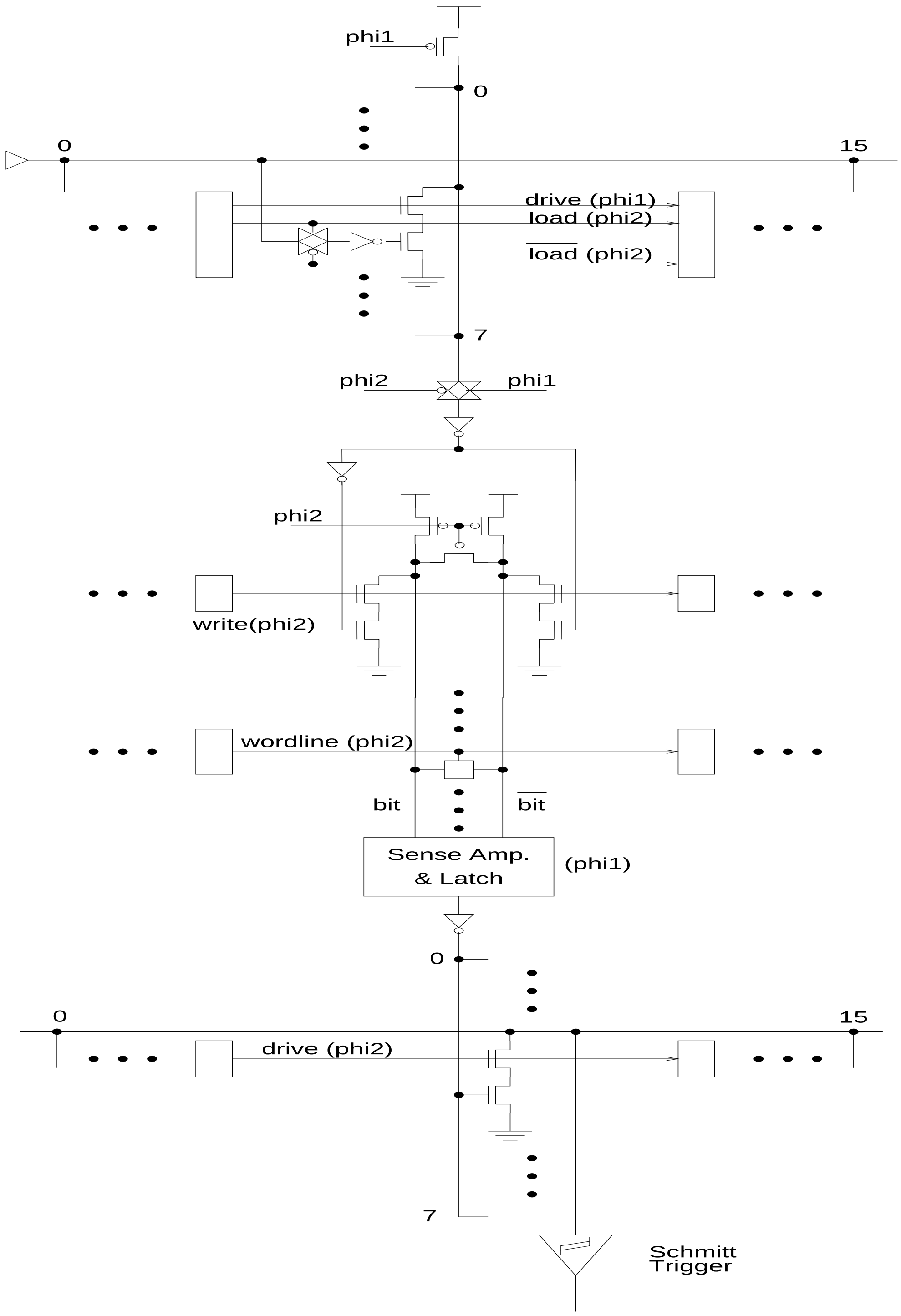


Figure 3.6: General circuit diagram.

for the reader's convenience.

Circuit	Activation phase
incoming link latch load	phi2
memory input bus: precharge	phi2
memory input bus: drive	phi1
bitline precharge and equalization	phi1
memory access, wordline drivers	phi2
sense amplifiers	phi1
outgoing link: precharge	phi1
outgoing link: drive	phi2

Table 3.2: Clock phases when the basic operations are performed.

Signal	Phase	Active
incoming link **load**	phi2	high
incoming link **loadBar**	phi2	low
memory input **drive**	phi1	high
write	phi2	high
outgoing link **drive**	phi2	high

Table 3.3: Clock phase and polarity of clock qualified control signals.

3.3.1 Memory circuits

The circuits that make up the memory blocks are SRAM cells, sense amplifiers, bitline drivers, the decoder, and the wordline pipeline latches.

SRAM Cell

We use the 6-transistor static memory cell, whose layout is shown in figure 3.7, as the building block of the memory arrays. Its size is $19.5\mu m \times 19.5\mu m$ and it has its contacts and wires along its perimeter shared with the adjacent cells. In the memory array, the ground lines are vertical, since they should always run in the bitline direction, while the supply lines are horizontal; they are connected at both of their ends to larger supply lines. We chose to run the bitlines in the second metal layer, because this layer, being farther from the substrate, has less capacitance than metal 1, and bitline capacitance is the most significant contributor to the memory access time. As a result of this decision, the ground lines, which also have a vertical direction use the second metal layer too, and the horizontal wordlines and VDD supply lines use the first metal layer. We included substrate and well contacts in each memory cell as an extra safeguard from latchup. Finally, we gained a reduction in bitline capacitance by sharing the drain area of each

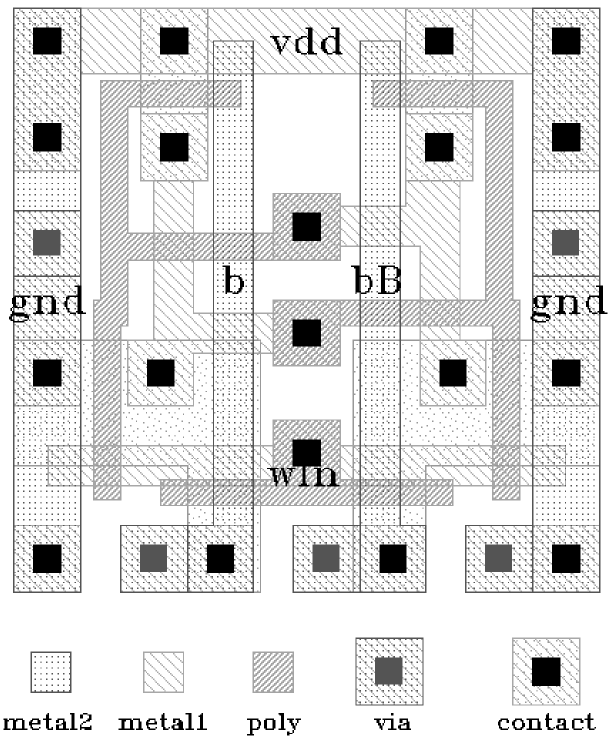


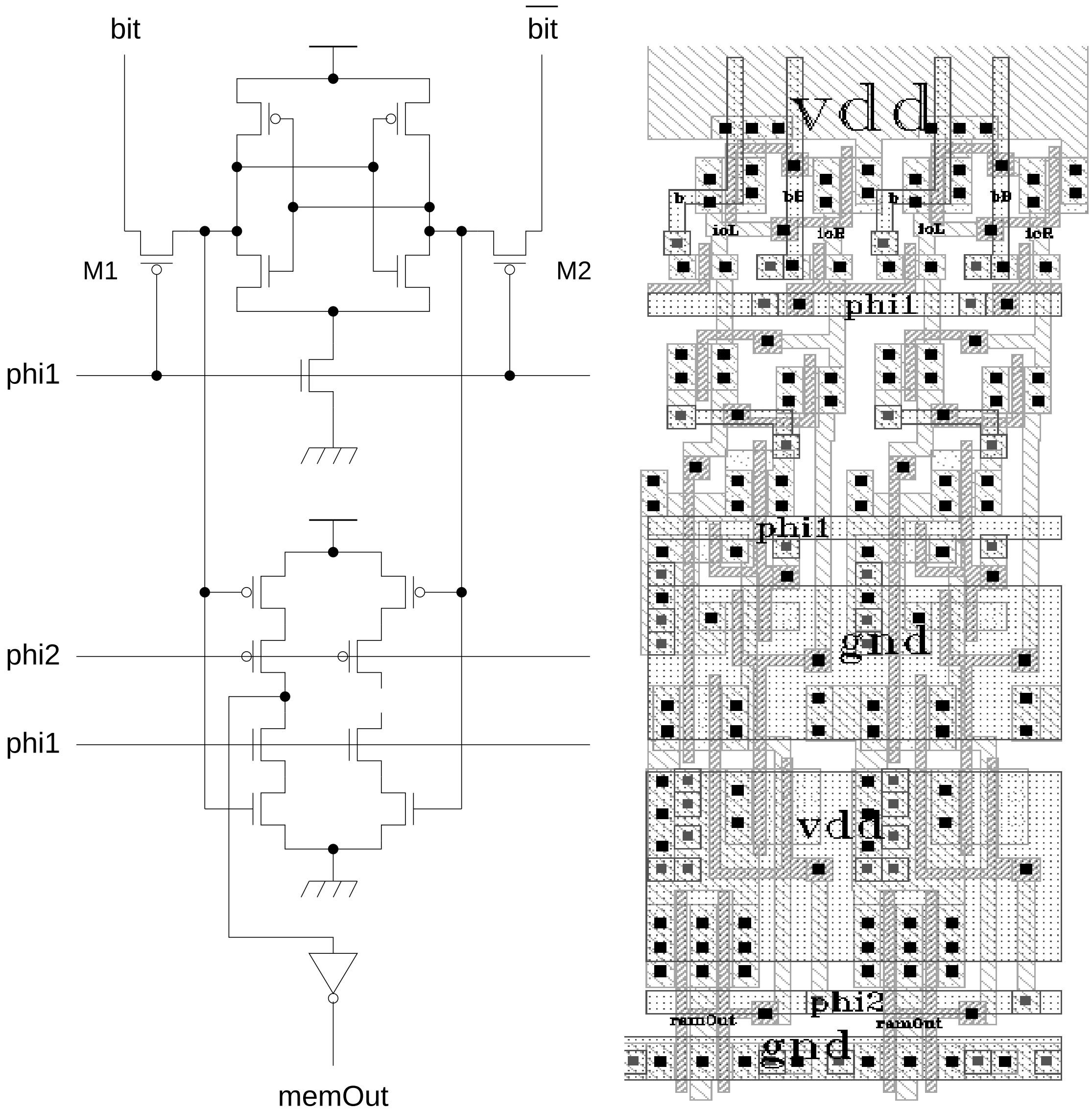
Figure 3.7: Layout of the SRAM memory cell.

pair of pass transistors that belong to vertically adjacent memory cells.

Sense Amplifier

Figure 3.8 shows the sense amplifier and latch schematic and layout. It consists of the differential sense amplifier itself, a latch, and an inverter driver for the memory output data line. This classical amplifier ([GrHo86] and [WeEs93]) consists of two inverters connected back-to-back. It employs positive feedback to achieve a very high gain, which makes the amplifier outputs reach the supply voltages very fast. When this happens, the amplifier stops consuming power, and behaves as a static latch.

During the phi2 phase of each cycle, the two PMOS pass transistors M1 and M2 are on and connect the sense amplifier terminals to the bitlines. Since the bitline capacitances are much larger than those of the sense amplifier terminals, charge sharing does not significantly affect the voltage of the bitlines, which in this phase are slewed by a memory cell, for read cycles, or the bitline drivers, for writes. At the same time the cross-coupled inverters' path to ground is cut by an NMOS transistor, disabling the amplifier. When the next phase starts, the PMOS pass transistors disconnect the amplifier's terminals from the bitlines and the amplifier's path



(a) Schematic (b) Layout of two cells

Figure 3.8: Sense amplifier, latch and memory output driver.

to the ground is re-established. The voltage difference at the amplifier terminals grows quickly due the positive feedback loop and within a few nanoseconds the terminals reach the supply and ground potentials. From this time on, the circuit behaves as a static latch, until it is reset at the next phi2 phase, by cutting its path to the ground and shorting its terminals to the bitlines.

P-type pass MOSFETs were chosen to connect the bitlines to the amplifier terminals instead of transmission gates or n-type MOSFETs, because the bitlines are usually at high potential (close to the 5 Volts supply voltage) which does not pass efficiently through n-type transistors. Thus, the NMOS transistors of the transmission gates would be useless, while the amplifier would not function for reads if only n-type pass transistors were used. During write accesses, when one of the bitlines is pulled down close to the ground potential, the p-type MOSFET connected to this bitlines cannot pull the corresponding amplifier terminal to the same low voltage, but this is not important as the voltage difference between the amplifier's terminals will be high enough to ensure its correct operation.

The layout of the sense amplifier was drawn very carefully, so that the transistor sources of the two cross-coupled inverters are on the same side of the gate, and similarly for the two drains. This ensures good matching even in case of mask misalignments during chip fabrication. Care was taken to match the capacitances of the amplifier outputs, so, although only one of the outputs is needed, we also feed the other amplifier output to a "dummy latch". Due to the limited space of the cell layout, this "dummy latch" was left with two chains of NMOS and PMOS transistors unconnected, as can be seen in figure 3.8(a). With this change, the two clock-controlled transistors do not serve any purpose and could have been omitted to decrease the capacitance on the clock wires. Moreover, the capacitance matching of the two sense amplifier terminals is not perfect due to the use of different latches, as the Miller capacitance is not present in the "dummy latch". This mismatch is insignificant though, because the capacitance due to the Miller effect is much less pronounced for a two (or more) transistor chain.

Many other alternatives were investigated for the sense amplifier circuit but we rejected them due to static power consumption (CMOS differential amplifiers e.g. that of [WeEs93]) or due to their complexity, e.g. [Seki93].

Bit-Line Drivers

The bitline driver cell is shown in figure 3.9. It consists of two parts: the bitline precharge circuits and the write circuits. Two PMOS transistors (M1 and M2) precharge the bitlines at phi1 towards the 5 volts supply voltage. In the same clock phase, another PMOS (M3) shorts the two bitlines together to equalize their voltage, which is essential for the correct operation of the sense amplifier. This last transistor shortens the bitline precharging time, especially after write accesses, when one of the bitlines had been discharged. The write circuits are two NMOS transistors in series, for each bitline. One end of this two transistor chain is connected to a bitline and the other end to the ground. The gates of M5 and M7 are controlled by the write signal which is a qualified clock active in phi2, when a write access is taking place. The other two NMOS transistors M4 and M6 are controlled by the memory data input bus, with the correct polarity for each of the two transistor gates. Most of the transistors in this cell are very large so as to achieve fast memory accesses; in the layout most of them are broken up to two or more parallel transistors, to make the layout more compact.

At an earlier stage of the design of this cell, an NMOS transistor was also used for shorting

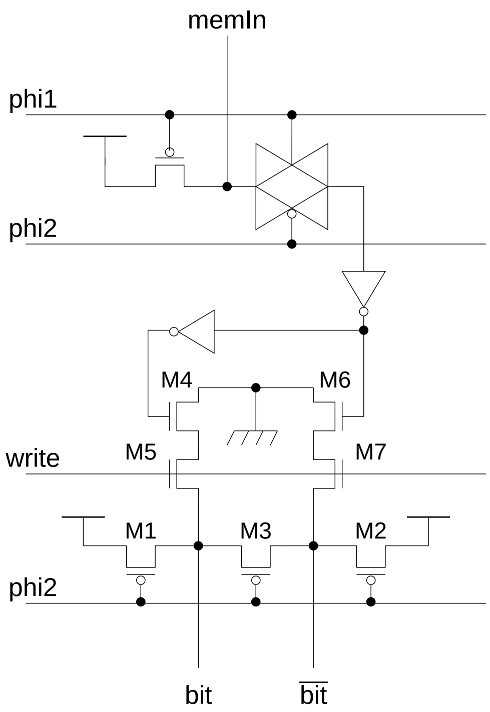


Figure 3.9: Bitline driver, memory input latch and precharge PMOSFETs.

the bitlines during the precharge phase in parallel with the PMOS one. This transistor speeds up the precharge operation but requires a different clock polarity from its PMOS counterpart, and we couldn't fit this extra clock driver in the very limited clock buffer cell area.

Wordline Pipeline Registers

The wordline or decoded address pipeline registers latch the wordlines of the previous memory stage and drive the wordlines of the current stage in phase phi2 of the next cycle. The schematic and the layout of one such cell can be seen in figures 3.10 and 3.11. We chose an edge-triggered register [YuKS87] (rising edge of phi1), instead of the usual two-phase tri-state dynamic latch, in order to only have to distribute one clock signal in the limited area of the wordline pipeline latches. Note that the two series PMOS transistors driving the wordline are adequate for the 16-bit long wordline of this implementation, but one may have to modify this driver if a larger memory word size is required. One interesting feature of the wordline driver is that it uses, in addition to the *phi1* controlled NMOS, another NMOS, controlled by the latched data, so that the wordline will not be left floating during *phi2* if it is not asserted.

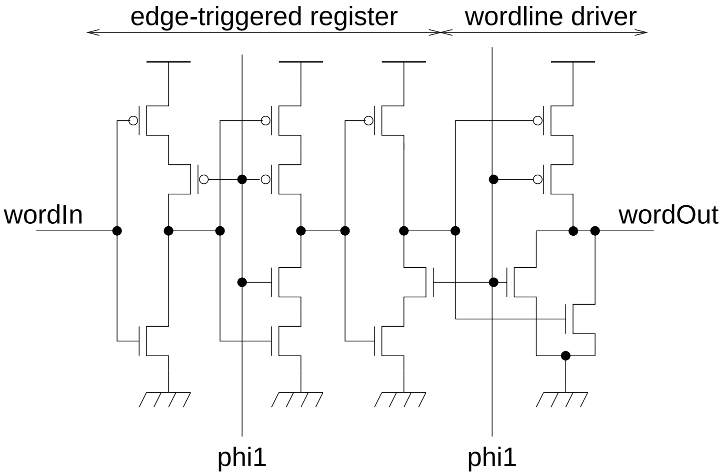


Figure 3.10: Wordline register and driver schematic.

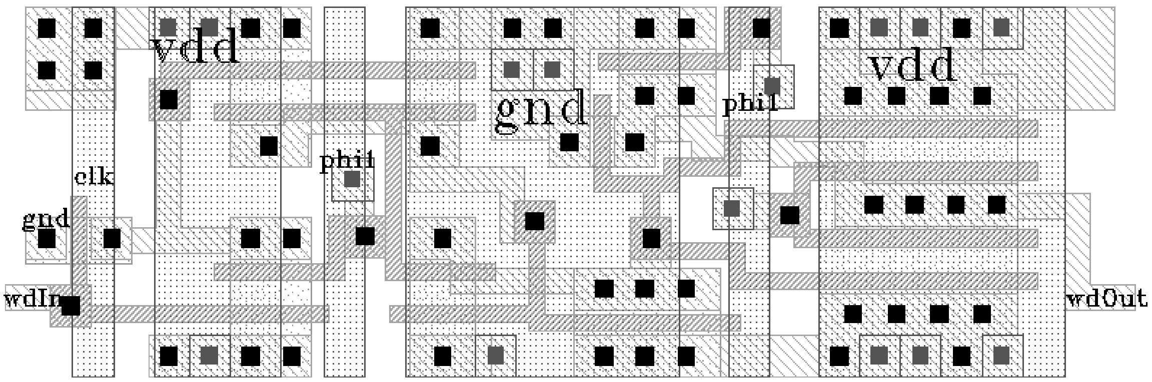


Figure 3.11: Wordline register and driver layout.

Decoder

The address decoder is a simple, 2-bit predecoded, 8 to 256 decoder. The decoder and predecoder basic circuits, along with the address latches, are shown in figures 3.12 and 3.13.

In the decoder circuit, although the basic *nand* gate is precharged, the classic *nand* PMOS transistors are also present. If these PMOS transistors weren't present, then the precharged *nand* would suffer from charge sharing between the *nand* output node and the small capacitors formed at the drains and sources of the NMOS transistor chain. We took care to make the redundant PMOS transistors of this *nand* small enough, so as not to load the address predecoder circuits too much.

Simulation

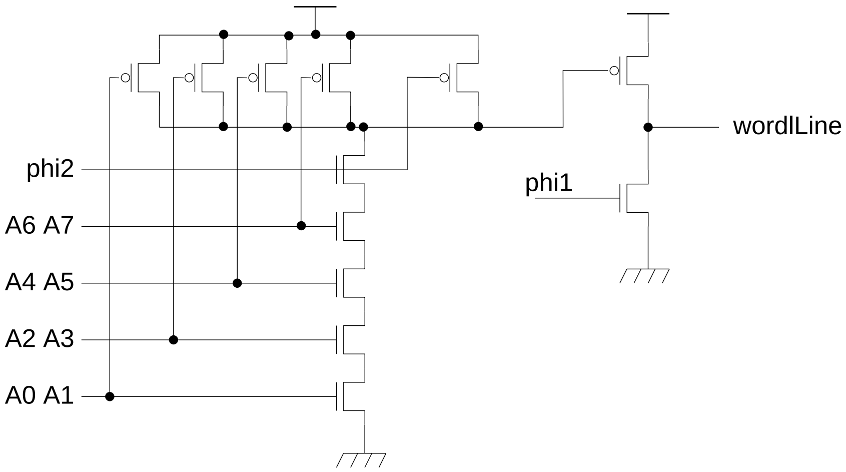


Figure 3.12: Decoder.

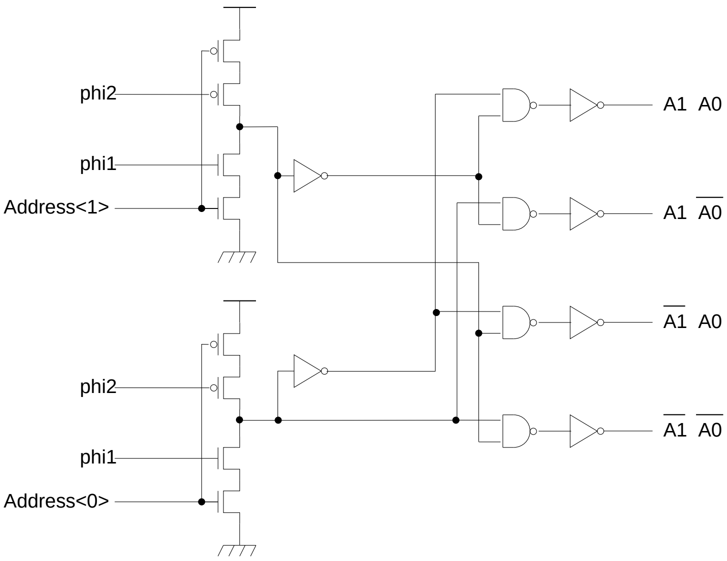


Figure 3.13: Predecoder and address latches.

Figure 3.14 shows the simulated operation of one stage of pipelined memory, in the worst operating conditions, i.e. 4.5 volts supply voltage, slow transistor models, high parasitics, and 125 degrees centigrade junction temperature. We present the waveforms of one pair of bitlines, the wordlines for two different words of memory, and the terminals of the sense amplifier that are connected to these bitlines. A write is performed, followed by a read of a cell with opposite data polarity which is connected to the same bitlines (**B** and **BBAR**). This read is then followed by another read of the previously written bit. The wordline waveforms (**WLN1, WLN2**) are produced by wordline pipeline latches and not from behavioural voltage sources. Of the sense amplifier terminals, **XSENSE.IOR** corresponds to **B** and **XSENSE.IOL** to **BBAR**. It can be clearly

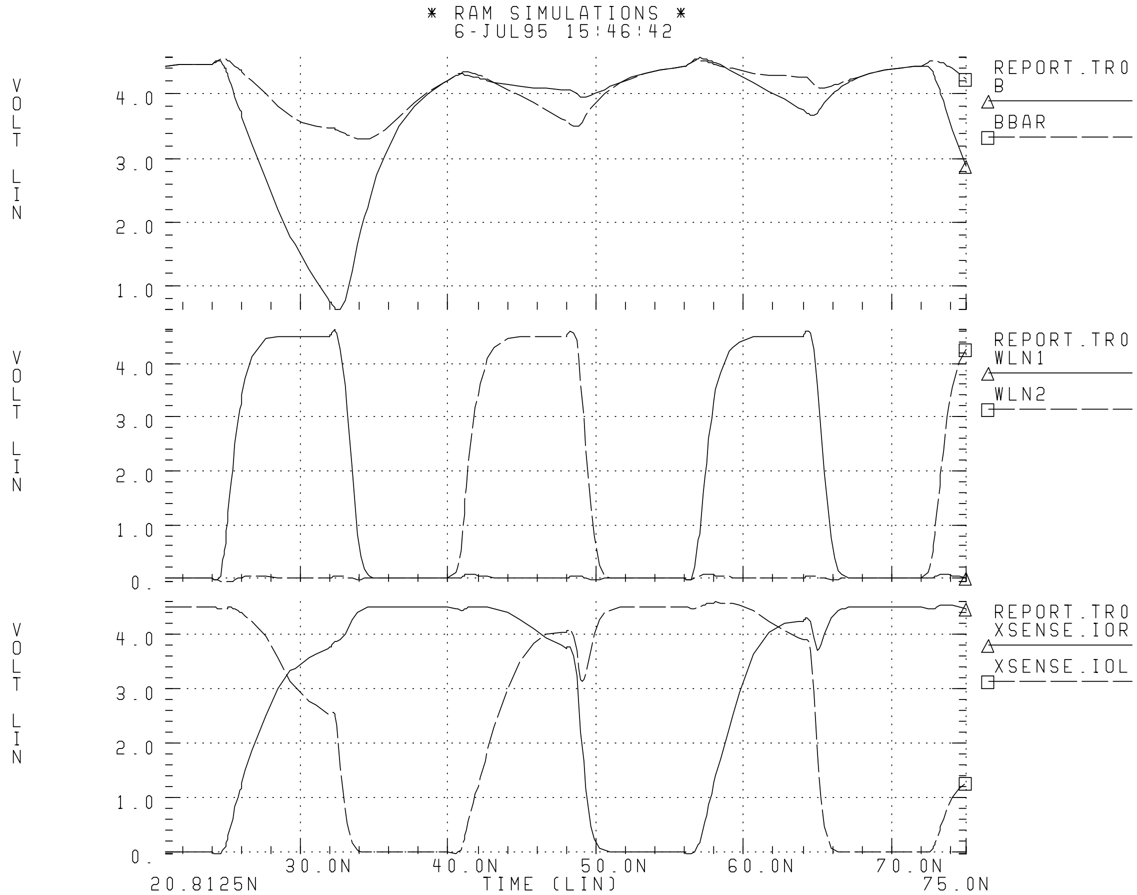


Figure 3.14: SRAM simulation.

seen at the time intervals 42ns to 48ns and 58ns to 64ns, when the memory cells drive the bitlines (at phi2), that the amplifier terminals have the same voltage with their respective bitlines. Within 2ns the sense amplifier has amplified its input and then behaves like a latch for the rest of the phi1 phase.

3.3.2 Incoming and Outgoing Links and Circuits

Incoming Links, Latches and Memory Input Drivers

The circuits associated with an incoming link consist of a tri-state dynamic latch and a memory input driver for each of the 16 bits of the link data bus, for each stage. The latch and driver for one bit are presented in figure 3.15. Packet data are stored in these latches for a short time, at most for as long as the reception of all the words of the packet, so dynamic circuits can be safely used. The two complementary load enable signals control all of the latches of the same

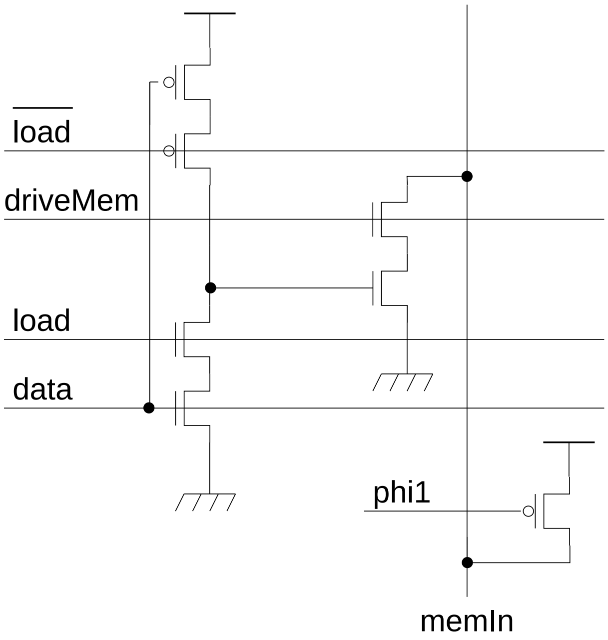


Figure 3.15: Incoming link latch and memory input driver.

link and stage, and are generated by the incoming link control signal pipeline latches. These load enables are qualified clocks, that is, they are active when a load enable is to take place and it is the right clock phase (phi2) to load the data. The memory input driver is just a chain of two N-type MOSFETs, which pull the precharged memory data input wire to the ground, when the corresponding latch holds a one and the qualified clock **driveMem** is high.

Physically, these circuits are placed under the incoming link wires, as can be seen in figure 3.16. With this layout, the incoming link circuit height[1] is 47% larger than that needed by the link data wires only, and 3.6% larger than that needed by data, control, and power wires. Note that due to the availability of only two metal layers in our technology and to the limited area for vertical wires, the power lines had to be run horizontally. The long link data wires, and thus all the horizontal wires of the incoming link area, are drawn in the second metal layer so as they have less capacitance and resistance than in metal 1. Care was also taken to share the drain of the memory input bus drivers between adjacent links in order to minimize the capacitance of the memory input wires.

Although there is some coupling between the incoming link data wires and the node where the latch stores the data, it is not possible for the latched data to be destroyed by this coupling. The maximum induced voltage when all of the link wires rise or fall within 1ns — which is almost impossible to achieve as they have large capacitance — is about 0.15 Volts. This voltage does not accumulate with time, as we show here. Imagine a rise in all of the link data wires which increases the potential of the storage node by 0.15 volts, due to the coupling effect.

[1]The width is pitch-matched to the memory.